

High Efficiency Standard Rectifier

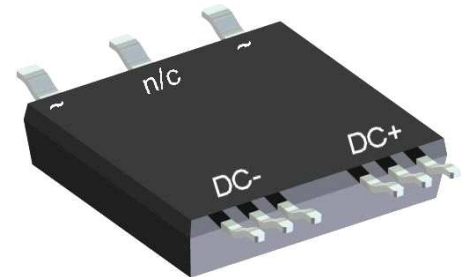
1~ Rectifier
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 124\text{ A}$
$I_{FSM} = 400\text{ A}$

1~ Rectifier Bridge

Part number

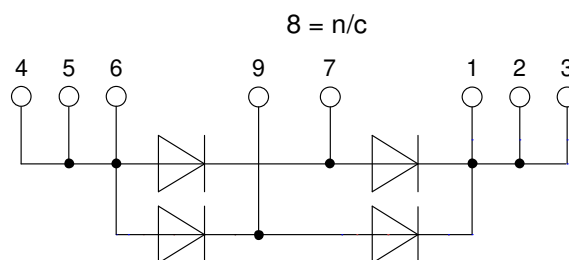
DLA100B1200LB

Marking on Product: DLA100B1200LB



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode Bridge for main rectification

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			10	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.1	mA
V_F	forward voltage drop	$I_F = 50\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.23	V
		$I_F = 100\text{ A}$				1.45	V
		$I_F = 50\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.15	V
		$I_F = 100\text{ A}$				1.44	V
I_{DAV}	bridge output current	$T_C = 135^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$			124	A
		180° sine					
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}\text{C}$			0.75	V
r_F	slope resistance					4.2	m Ω
R_{thJC}	thermal resistance junction to case					1	K/W
R_{thCH}	thermal resistance case to heatsink				0.40		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			150	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			400	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			430	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			340	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			365	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			800	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			770	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			580	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			555	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		13		pF

Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	A
T _{VJ}	virtual junction temperature			-55		175	°C
T _{op}	operation temperature			-55		150	°C
T _{stg}	storage temperature			-55		150	°C
Weight					8.5		g
F _C	mounting force with clip			40		130	N
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		1.6			mm
d _{Spb/Apb}		terminal to backside		4.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Part description

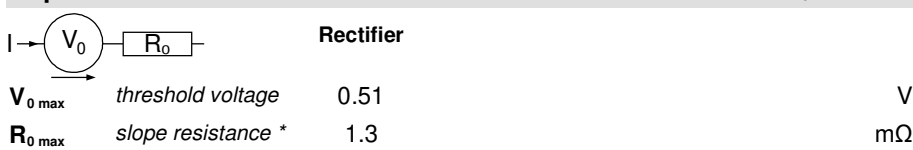
D = Diode
 L = Low Voltage Standard Rectifier
 A = (up to 1200V)
 100 = Current Rating [A]
 B = 1~ Rectifier Bridge
 1200 = Reverse Voltage [V]
 LB = SMPD-B

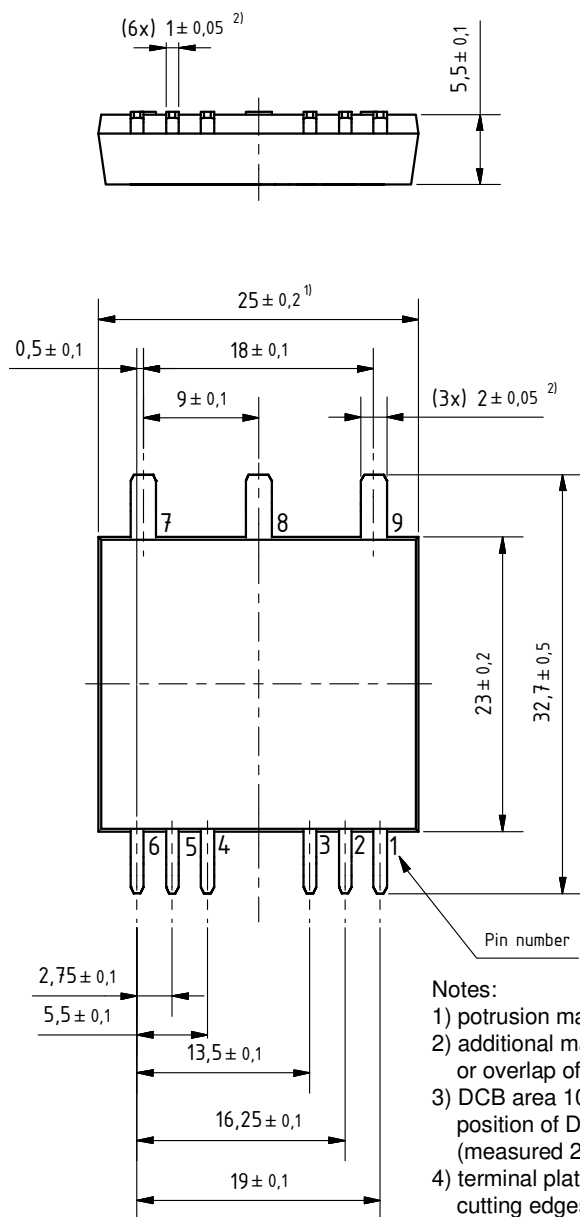
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA100B1200LB-TUB	DLA100B1200LB	Tube	20	517180
Alternative	DLA100B1200LB-TRR	DLA100B1200LB	Tape & Reel	200	517187

Equivalent Circuits for Simulation

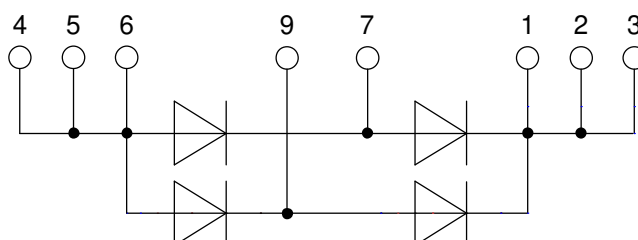
* on die level

$T_{VJ} = 175^\circ\text{C}$



Outlines SMPD
A (8 : 1)

Notes:

- 1) protrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignment or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 μm convex; position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$ (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 - 1 μm Ni + 10 - 25 μm Sn (gal v.) cutting edges may be partially free of plating

8 = n/c


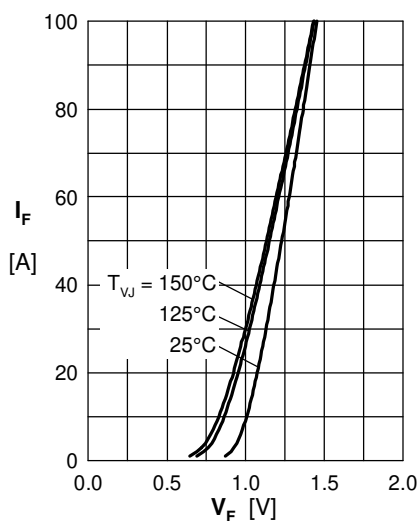
Rectifier


Fig. 1 Forward current versus voltage drop per diode

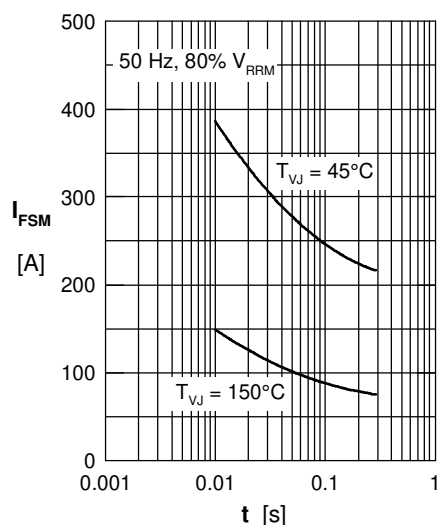


Fig. 2 Surge overload current

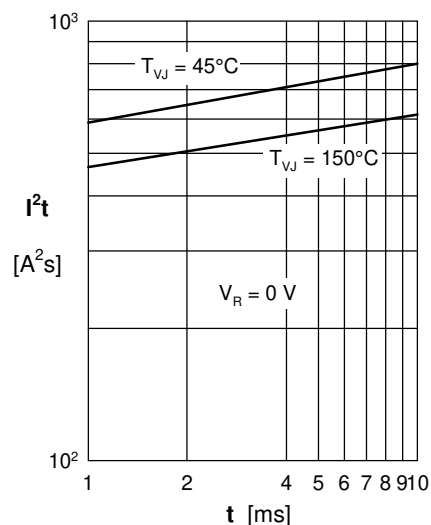


Fig. 3 I^2t versus time per diode

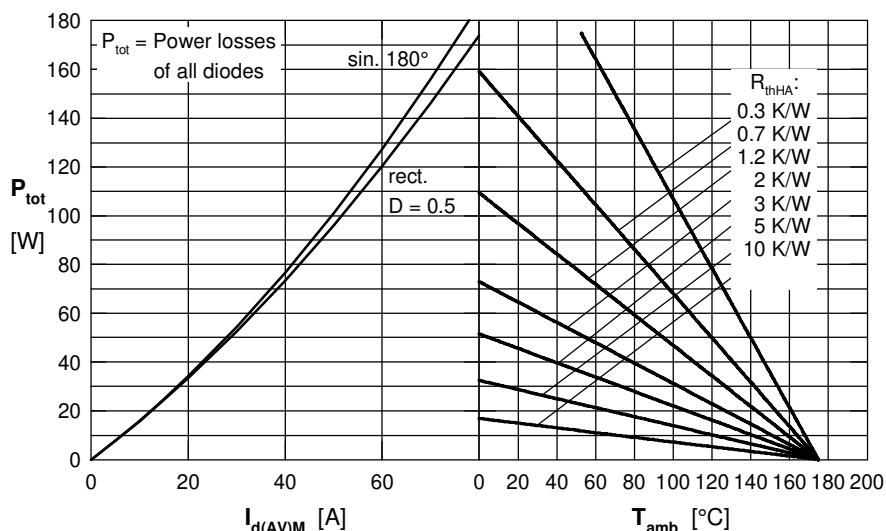


Fig. 4 Power dissipation vs. bridge output current and ambient temperature

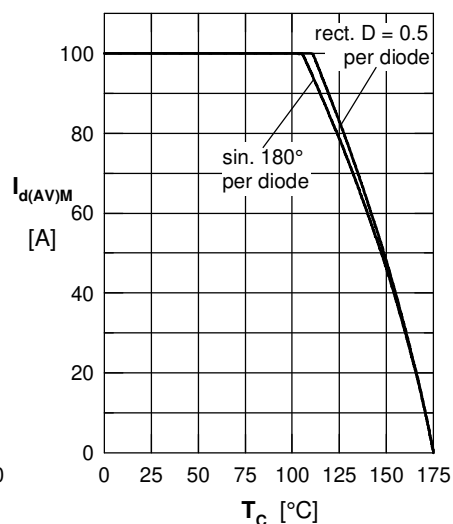


Fig. 5 Max. bridge output current vs. case temperature

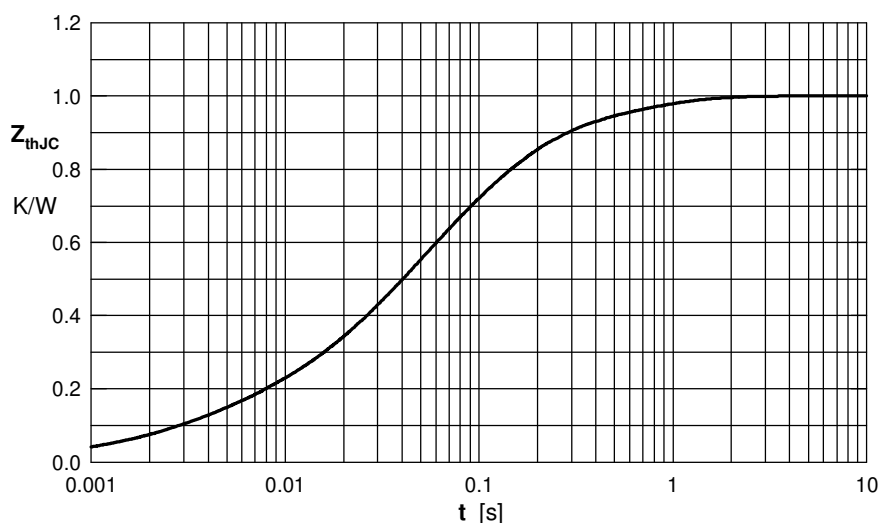


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.09	0.003
2	0.116	0.062
3	0.386	0.1
4	0.128	0.55